



20V LOW $V_{CE(SAT)}$ PNP SURFACE MOUNTED TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (ZXTN26020DMF)
- Low Collector-Emitter Saturation Voltage, V_{CE(SAT)}
- High Current Gain (hFE) at High IC
- Surface Mount Package Suited for Automated Assembly
- Ultra-Small Surface Mount Package
- Qualified to AEC-Q101 Standards for High Reliability
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM

Mechanical Data

- Case: DFN1411-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (approximate)

Applications

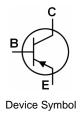
- MOSFET and IGBT gate driving
- DC-DC conversion
- Interface between low voltage IC and Load
- Load disconnect switch



Top view



Bottom view





Pin-Out Top view

Ordering Information

| Product | Reel size (inches) | Tape width (mm) | Quantity per reel |
|----------------|--------------------|-----------------|-------------------|
| ZXTP26020DMFTA | 7 | 8 | 3000 |

Notes: 1. No purposefully added lead. Halogen and Antimony Free.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



Z2= Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

| Date Code Key | |
|---------------|--|
|---------------|--|

| Year | 2009 | | 2010 | 2011 | | 2012 | 2013 | | 2014 | 2015 | | 2016 |
|-------|------|-----|------|------|-----|------|------|-----|------|------|-----|------|
| Code | W | | Х | Y | | Z | A | | В | С | | D |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |





Maximum Ratings

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | -20 | V |
| Collector-Emitter Voltage | V _{CEO} | -20 | V |
| Emitter-Base Voltage | V _{EBO} | -7 | V |
| Continuous Collector Current | lc | -1.25 | А |
| Peak Pulse Current | I _{CM} | -4 | А |
| Base Current(DC) | Ι _Β | -0.3 | А |
| Peak Base Current | I _{BM} | -0.6 | А |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|------------------------------------------------------------------------|------------------|-------------|------|
| Power Dissipation (Note 3) | PD | 1 | W |
| Power Dissipation (Note 4) | PD | 380 | mW |
| Thermal Resistance, Junction to Ambient (Note 3) @ $T_A = 25^{\circ}C$ | R _{θJA} | 125 | °C/W |
| Thermal Resistance, Junction to Ambient (Note 4) @ $T_A = 25^{\circ}C$ | $R_{\theta JA}$ | 330 | °C/W |
| Operating and Storage Temperature Range | TJ, TSTG | -55 to +150 | °C |

Notes:

Device mounted on FR-4 PCB with 1inch square pads.
Device mounted on FR-4 PCB with minimum recommended pad layout



Electrical Characteristics (at T_A = 25°C unless otherwise specified)

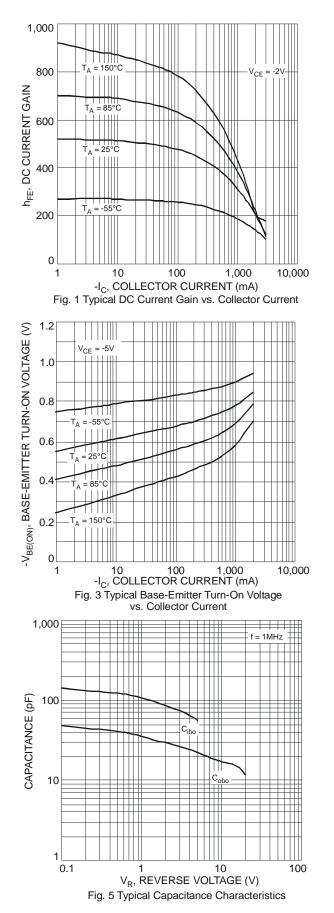
| | | | _ | | | |
|-----------------------------------------------|----------------------|-----|-----|-------|------|---------------------------------------------------------------|
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | -20 | — | | V | $I_{\rm C} = -100 \mu A, I_{\rm E} = 0 A$ |
| Collector-Emitter Breakdown Voltage (Note 5) | V _{(BR)CEO} | -20 | — | — | V | $I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0 {\rm A}$ |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | -7 | — | | V | $I_E = -100 \mu A, I_C = 0A$ |
| Collector Cutoff Current | Icbo | | | -100 | nA | $V_{CB} = -20V, I_E = 0A$ |
| | 1000 | | | -0.5 | μΑ | $V_{CB} = -20V, I_E = 0A, T_A = 125^{\circ}C$ |
| Emitter Cutoff Current | Ices | | — | -100 | nA | $V_{CE} = -20V, V_{BE} = 0V$ |
| Base Cutoff Current | lebo | — | _ | -50 | nA | $V_{BE} = -6V, I_{C} = 0A$ |
| | | 300 | _ | _ | | $V_{CE} = -2V, I_{C} = -100 \text{mA}$ |
| DC Current Gain (Note 5) | h | 235 | _ | | | $V_{CE} = -2V, I_{C} = -0.5A$ |
| DC Current Gain (Note 5) | h _{FE} | 175 | — | — | | $V_{CE} = -2V, I_{C} = -1A$ |
| | | 140 | — | | | $V_{CE} = -2V, I_{C} = -1.5A$ |
| | | | | | | |
| | | — | — | -80 | mV | $I_{\rm C} = -100 {\rm mA}, I_{\rm B} = -1 {\rm mA}$ |
| Collector-Emitter Saturation Voltage (Note 5) | V _{CE(SAT)} | — | — | -100 | mV | $I_{\rm C} = -500 {\rm mA}, I_{\rm B} = -50 {\rm mA}$ |
| g- (····· -) | · CE(GAT) | — | — | -155 | mV | $I_{\rm C} = -1A, I_{\rm B} = -50 {\rm mA}$ |
| | | _ | _ | -235 | mV | $I_{\rm C}$ = -1.25A, $I_{\rm B}$ = -62.5mA |
| Equivalent On-Resistance | R _{CE(SAT)} | _ | 125 | | mΩ | I _C = -1A, I _B = -50mA |
| Base-Emitter Turn-On Voltage | V _{BE(ON)} | _ | _ | -1.1 | V | $V_{CE} = -5V, I_{C} = -1A$ |
| Base-Emitter Saturation Voltage | V _{BE(SAT)} | _ | _ | -1.15 | V | I _C = -1A, I _B = -50mA |
| Output Capacitance (Note 5) | C _{obo} | | _ | 20 | pF | V _{CB} = -10V, f = 1.0MHz |
| Current Gain-Bandwidth Product | fT | 200 | _ | _ | MHz | V _{CE} = -10V, I _C = -50mA, f = 100MHz |
| Turn-On Time | t _{on} | | 60 | | ns | |
| Delay Time | t _d | | 20 | | ns | 7 |
| Rise Time | tr | — | 40 | | ns | $V_{CC} = -10V, I_{C} = -1A$ |
| Turn-Off Time | toff | — | 167 | | ns | $I_{B2} = -I_{B1} = -50 \text{mA}$ |
| Storage Time | ts | — | 140 | _ | ns | 1 |
| Fall Time | tf | _ | 27 | _ | ns | 7 |

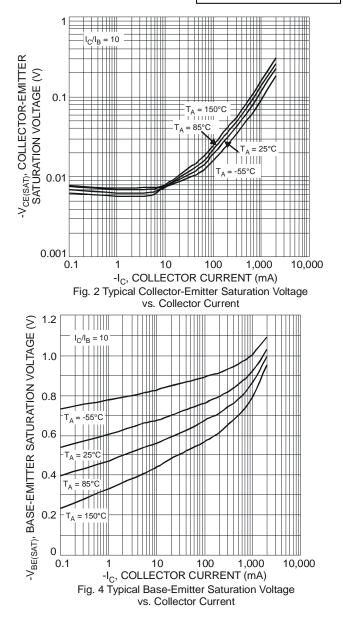
Notes: 5. Short duration pulse test used to minimize self-heating effect.





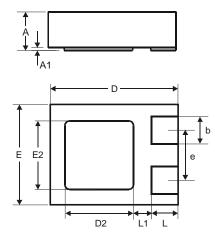






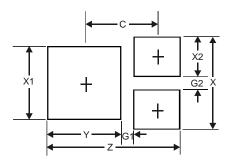


Package Outline Dimensions



| DFN1411-3 | | | | | | |
|-----------|----------------------|-------|-------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.47 | 0.53 | 0.50 | | | |
| A1 | 0 | 0.05 | 0.02 | | | |
| b | 0.25 | 0.35 | 0.30 | | | |
| D | 1.35 | 1.475 | 1.40 | | | |
| D2 | 0.65 | 0.85 | 0.75 | | | |
| Е | 1.05 | 1.18 | 1.10 | | | |
| E2 | 0.65 | 0.85 | 0.75 | | | |
| е | | | 0.55 | | | |
| L | 0.225 | 0.325 | 0.275 | | | |
| L1 | | | 0.20 | | | |
| All D | All Dimensions in mm | | | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 1.38 |
| G1 | 0.15 |
| G2 | 0.15 |
| Х | 0.95 |
| X1 | 0.75 |
| X2 | 0.40 |
| Ŷ | 0.75 |
| С | 0.76 |



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